EAST SEARCH

9/5/03

L#	Hits	Search String	Databases
L2	2	3,751,647.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	3	3,842,491.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	2	5,432,587.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L5	2	5,815,404.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L7	2	6,499,007.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L9	429309	(integrated or digital) adj circuit$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L10	508	((integrated or digital) adj circuit$1) and (simulat$3 with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L11	0	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with "photolithographic mask")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L12	1	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 same "photolithographic mask")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L13	118	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L2	28	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with "optical pr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	18	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("photolithographic mask"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	12	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("photolithographic mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L5	99	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask witl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L6	13	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask witl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L8	15	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with "optical pr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L7	5	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (correct$3 with "corner ro	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L9	7	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("optical proximity" same	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L10	1	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("optical proximity" with lig	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L11	80	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask witl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	67	(((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask wi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	57	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with (photolithe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	3	6,453,452.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	0	6,453,452.pn. and (light with wavelength)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	508	((integrated or digital) adj circuit$1) and (simulat$3 with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	58	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("optical proximity" and (lig	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	22	ted or digital) adj circuit$1) and (simulat$3 with mask)) and (light with wavelength) and (image	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	13	optical proximity" and (light with wavelength))) and ((((integrated or digital) adj circuit$1) and (s	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	12	Fang-Cheng Chang	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L1	429309	(integrated or digital) adj circuit$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L2	646	1 and "optical proximity"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	214	2 and "proximity effects"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	12	2 and ("proximity effects" same (light with wavelength))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

L1	429343	(integrated or digital) adj circuit$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L2	22	1 and (subwavelength and (lothography or photolithography))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	1	2 and (wavelength with light with feature with size$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	18	2 and (wavelength with light)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L5	15	2 and (feature with size$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L6	12	4 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	618	((integrated or digital) adj circuit$1) and (simulat$3 with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	151	((integrated or digital) adj circuit$1) and (simulat$3 with mask with image)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	128	(((integrated or digital) adj circuit$1) and (simulat$3 with mask with image)) and ((correct$3 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	53	((((integrated or digital) adj circuit$1) and (simulat$3 with mask with image)) and ((correct$3 o	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	11	((((integrated or digital) adj circuit$1) and (simulat$3 with mask with image)) and ((correct$3 o	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	139	((integrated or digital) adj circuit$1) and (simulat$3 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	18	((integrated or digital) adj circuit$1) and ((simulat$3 near2 mask) with layout)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L13	8	Mask verification adj correction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L14	139	((integrated or digital) adj circuit$1) and (simulat$3 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L15	8	13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L16	18	((integrated or digital) adj circuit$1) and ((simulat$3 near2 mask) with layout)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L17	4	13 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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Results of search set L10:((integrated or digital) adj circuit$1) and (simulat$3 with (photolithograph$2 or lithograph$2) with mask)

Document	Kind Code	Title	Issue Date	Current OR	Abstract
US 20030126581	A1	User interface for a network-based mask defect printability analysis system	20030703	716/19	
US 20030119216	A1	Simulation-based feed forward process control	20030626	438/14	
US 20030115569	A1	Method and system for optical proximity correction	20030619	716/19	
US 20030093251	A1	Simulation using design geometry information	20030515	703/13	
US 20030077526	A1	Two-exposure phase shift photolithography with improved inter-feature separation	20030424	430/5	
US 20030068564	A1	System and method for correcting 3D effects in an alternating phase-shifting mask	20030410	430/5	
US 20030014146	A1	Dangerous process/pattern detection system and method, danger detection program, and sen	20030116	700/121	
US 20020164065	A1	System and method of providing mask defect printability analysis	20021107	382/149	
US 20020164064	A1	System and method of providing mask quality control	20021107	382/145	
US 20020152452	A1	Illumination optimization for specific mask patterns	20021017	716/21	
US 20020094492	A1	Two-exposure phase shift photolithography with improved inter-feature separation	20020718	430/311	
US 20020091986	A1	Process window based optical proximity correction of lithographic images	20020711	716/19	
US 20020086218	A1	Optical assist feature for two-mask exposure lithography	20020704	430/5	
US 20020083408	A1	Generating mask layout data for simulation of lithographic processes	20020627	716/19	

US 20020062206 A1	Method and apparatus for fast aerial image simulation	20020523	703/6
US 20020035461 A1	Visual analysis and verification system using advanced tools	20020321	703/13
US 20020019729 A1	VISUAL INSPECTION AND VERIFICATION SYSTEM	20020214	703/6
US 20020002697 A1	Semiconductor integrated circuit designing method and system	20020103	716/2
US 6605481 B1	Facilitating an adjustable level of phase shifting during an optical lithography process for manu	20030812	438/14
US 6578190 B2	Process window based optical proximity correction of lithographic images	20030610	716/21
US 6578188 B1	Method and apparatus for a network-based mask defect printability analysis system	20030610	716/19
US 6577994 B1	Design rule generation system and recording medium recording program thereof	20030610	703/15
US 6562638 B1	Integrated scheme for predicting yield of semiconductor (MOS) devices from designed layout	20030513	438/14
US 6560766 B2	Method and apparatus for analyzing a layout using an instance-based representation	20030506	716/19
US 6541770 B1	Charged particle system error diagnosis	20030401	250/310
US 6507931 B2	Semiconductor integrated circuit designing method and system	20030114	716/2
US 6470489 B1	Design rule checking system and method	20021022	716/21
US 6363167 B1	Method for measuring size of fine pattern	20020326	382/145
US 6261724 B1	Method of modifying a microchip layout data set to generate a predicted mask printed data set	20010717	430/5
US 6249597 B1	Method of correcting mask pattern and mask, method of exposure, apparatus thereof, and phc	20010619	382/144
US 6223139 B1	Kernel-based fast aerial image computation for a large scale design of integrated circuit patter	20010424	703/5
US 6154563 A	Method of correcting mask pattern and mask, method of exposure, apparatus thereof, and phc	20001128	382/144
US RE36964 E	Device manufacture involving lithographic processing	20001121	430/296
US 6128067 A	Correcting method and correcting system for mask pattern	20001003	355/52
US 6096457 A	Method for optimizing printing of a phase shift mask having a phase shift error	20000801	430/5
US 6077310 A	Optical proximity correction system	20000620	716/19
US 6067375 A	Correction method and correction apparatus of mask pattern	20000523	382/144
US 6058203 A	Correction method and correction apparatus of mask pattern	20000502	382/144
US 6042257 A	Correction method and correction apparatus of mask pattern	20000328	700/121
US 6014456 A	Method of correcting mask pattern and mask, method of exposure, apparatus thereof, and phc	20000111	382/144
US 5998070 A	Mask pattern	19991207	430/5
US 5986292 A	Semiconductor integrated logic circuit device	19991116	257/202
US 5969801 A	Correction method and correction apparatus of mask pattern	19991019	355/55
US 5952160 A	Method and system for controlling the relative size of images formed in light-sensitive media	19990914	430/394
US 5928813 A	Attenuated phase shift mask	19990727	430/5
US 5879844 A	Optical proximity correction method	19990309	430/30
US 5825647 A	Correction method and correction apparatus of mask pattern	19981020	700/57
US 5764342 A	Method and system for controlling the relative size of images formed in light-sensitive media	19980609	355/53
US 5725974 A	Method and apparatus for producing scanning data used to produce a photomask	19980310	430/5
US 5635285 A	Method and system for controlling the relative size of images formed in light-sensitive media	19970603	428/195.1
US 5601954 A	Attenuated phase shift mask comprising phase shifting layer with parabolically shaped sidewa	19970211	430/5
US 5502654 A	Method for analyzing light intensity distribution in projection systems	19960326	382/280
US 5246800 A	Discrete phase shift mask writing	19930921	430/5
US 5173864 A	Standard cell and standard-cell-type integrated circuit	19921222	716/6
US 20020091986 A	Mask pattern creating method in lithographic production of integrated circuit, involves compari	20030610	
EP 1193552 A	Generating mask layout data for lithographic simulation involves computing new data based o	20020801	
US 20020019729 A	Method for inspecting mask used in lithography for defects using partial mask defect image ar	19990325	

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L2	2	3,751,647.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
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L4	2	5,432,587.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L5	2	5,815,404.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L7	2	6,499,007.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L9	429309	(integrated or digital) adj circuit$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L10	508	((integrated or digital) adj circuit$1) and (simulat$3 with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L11	0	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with "photolithographic mask")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L12	1	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 same "photolithographic mask")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L13	118	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L2	28	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with "optical pr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	18	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("photolithographic mask"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	12	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("photolithographic mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L5	99	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask witl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L6	13	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask witl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L8	15	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with "optical pr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L7	5	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (correct$3 with "corner ro	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L9	7	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("optical proximity" same	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L10	1	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("optical proximity" with lig	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L11	80	((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask witl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	67	(((((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with mask wi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	57	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and (simulat$3 with (photolith	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	3	6,453,452.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	0	6,453,452.pn. and (light with wavelength)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	508	((integrated or digital) adj circuit$1) and (simulat$3 with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	58	(((integrated or digital) adj circuit$1) and (simulat$3 with mask)) and ("optical proximity" and (li	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	22	ted or digital) adj circuit$1) and (simulat$3 with mask)) and (light with wavelength) and (image	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	13	optical proximity" and (light with wavelength))) and ((((integrated or digital) adj circuit$1) and (s	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	12	Fang-Cheng Chang	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L1	429309	(integrated or digital) adj circuit$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L2	646	1 and "optical proximity"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	214	2 and "proximity effects"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	12	2 and ("proximity effects" same (light with wavelength))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

L1	429343	(integrated or digital) adj circuit$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L2	22	1 and (subwavelength and (lothography or photolithography))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L3	1	2 and (wavelength with light with feature with size$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L4	18	2 and (wavelength with light)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L5	15	2 and (feature with size$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
L6	12	4 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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Results of search set L10:((integrated or digital) adj circuit$1) and (simulat$3 with (photolithograph$2 or lithograph$2) with mask)

DocumentKind Codes	Title	Issue Date	Current OR	Abstract
US 20030126581 A1	User interface for a network-based mask defect printability analysis system	20030703	716/19	
US 20030119216 A1	Simulation-based feed forward process control	20030626	438/14	
US 20030115569 A1	Method and system for optical proximity correction	20030619	716/19	
US 20030093251 A1	Simulation using design geometry information	20030515	703/13	
US 20030077526 A1	Two-exposure phase shift photolithography with improved inter-feature separation	20030424	430/5	
US 20030068564 A1	System and method for correcting 3D effects in an alternating phase-shifting mask	20030410	430/5	
US 20030014146 A1	Dangerous process/pattern detection system and method, danger detection program, and sen	20030116	700/121	
US 20020164065 A1	System and method of providing mask defect printability analysis	20021107	382/149	
US 20020164064 A1	System and method of providing mask quality control	20021107	382/145	
US 20020152452 A1	Illumination optimization for specific mask patterns	20021017	716/21	
US 20020094492 A1	Two-exposure phase shift photolithography with improved inter-feature separation	20020718	430/311	
US 20020091986 A1	Process window based optical proximity correction of lithographic images	20020711	716/19	
US 20020086218 A1	Optical assist feature for two-mask exposure lithography	20020704	430/5	
US 20020083408 A1	Generating mask layout data for simulation of lithographic processes	20020627	716/19	
US 20020062206 A1	Method and apparatus for fast aerial image simulation	20020523	703/6	
US 20020035461 A1	Visual analysis and verification system using advanced tools	20020321	703/13	
US 20020019729 A1	VISUAL INSPECTION AND VERIFICATION SYSTEM	20020214	703/6	
US 20020002697 A1	Semiconductor integrated circuit designing method and system	20020103	716/2	
US 6605481 B1	Facilitating an adjustable level of phase shifting during an optical lithography process for mani	20030812	438/14	
US 6578190 B2	Process window based optical proximity correction of lithographic images	20030610	716/21	
US 6578188 B1	Method and apparatus for a network-based mask defect printability analysis system	20030610	716/19	
US 6577994 B1	Design rule generation system and recording medium recording program thereof	20030610	703/15	
US 6562638 B1	Integrated scheme for predicting yield of semiconductor (MOS) devices from designed layout	20030513	438/14	
US 6560766 B2	Method and apparatus for analyzing a layout using an instance-based representation	20030506	716/19	
US 6541770 B1	Charged particle system error diagnosis	20030401	250/310	
US 6507931 B2	Semiconductor integrated circuit designing method and system	20030114	716/2	
US 6470489 B1	Design rule checking system and method	20021022	716/21	
US 6363167 B1	Method for measuring size of fine pattern	20020326	382/145	

US 6261724 B1	Method of modifying a microchip layout data set to generate a predicted mask printed data se	20010717	430/5
US 6249597 B1	Method of correcting mask pattern and mask, method of exposure, apparatus thereof, and ph	20010619	382/144
US 6223139 B1	Kernel-based fast aerial image computation for a large scale design of integrated circuit patte	20010424	703/5
US 6154563 A	Method of correcting mask pattern and mask, method of exposure, apparatus thereof, and ph	20001128	382/144
US RE36964 E	Device manufacture involving lithographic processing	20001121	430/296
US 6128067 A	Correcting method and correcting system for mask pattern	20001003	355/52
US 6096457 A	Method for optimizing printing of a phase shift mask having a phase shift error	20000801	430/5
US 6077310 A	Optical proximity correction system	20000620	716/19
US 6067375 A	Correction method and correction apparatus of mask pattern	20000523	382/144
US 6058203 A	Correction method and correction apparatus of mask pattern	20000502	382/144
US 6042257 A	Correction method and correction apparatus of mask pattern	20000328	700/121
US 6014456 A	Method of correcting mask pattern and mask, method of exposure, apparatus thereof, and ph	20000111	382/144
US 5998070 A	Mask pattern	19991207	430/5
US 5986292 A	Semiconductor integrated logic circuit device	19991116	257/202
US 5969801 A	Correction method and correction apparatus of mask pattern	19991019	355/55
US 5952160 A	Method and system for controlling the relative size of images formed in light-sensitive media	19990914	430/394
US 5928813 A	Attenuated phase shift mask	19990727	430/5
US 5879844 A	Optical proximity correction method	19990309	430/30
US 5825647 A	Correction method and correction apparatus of mask pattern	19981020	700/57
US 5764342 A	Method and system for controlling the relative size of images formed in light-sensitive media	19980609	355/53
US 5725974 A	Method and apparatus for producing scanning data used to produce a photomask	19980310	430/5
US 5635285 A	Method and system for controlling the relative size of images formed in light-sensitive media	19970603	428/195.1
US 5601954 A	Attenuated phase shift mask comprising phase shifting layer with parabolically shaped sidewa	19970211	430/5
US 5502654 A	Method for analyzing light intensity distribution in projection systems	19960326	382/280
US 5246800 A	Discrete phase shift mask writing	19930921	430/5
US 5173864 A	Standard cell and standard-cell-type integrated circuit	19921222	716/6
US 20020091986 A	Mask pattern creating method in lithographic production of integrated circuit, involves compari	20030610	
EP 1193552 A	Generating mask layout data for lithographic simulation involves computing new data based o	20020801	
US 20020019729 A	Method for inspecting mask used in lithography for defects using partial mask defect image ar	19990325	